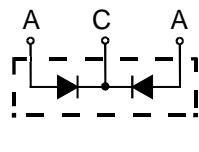
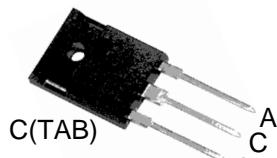


MBR30100PT thru MBR30200PT

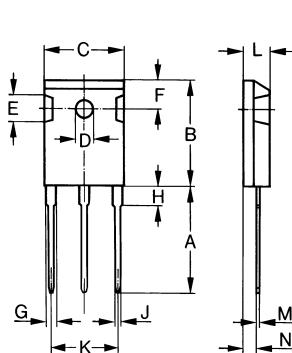
Wide Temperature Range and High $T_{j\text{m}}$ Schottky Barrier Rectifiers



A=Anode, C=Cathode, TAB=Cathode

| | V_{RRM} V | V_{RMS} V | V_{DC} V |
|-------------------|----------------|----------------|---------------|
| MBR30100PT | 100 | 70 | 100 |
| MBR30150PT | 150 | 105 | 150 |
| MBR30200PT | 200 | 140 | 200 |

Dimensions TO-247AD



| Dim. | Millimeter Min. | Millimeter Max. | Inches Min. | Inches Max. |
|------|--------------------|--------------------|----------------|----------------|
| A | 19.81 | 20.32 | 0.780 | 0.800 |
| B | 20.80 | 21.46 | 0.819 | 0.845 |
| C | 15.75 | 16.26 | 0.610 | 0.640 |
| D | 3.55 | 3.65 | 0.140 | 0.144 |
| E | 4.32 | 5.49 | 0.170 | 0.216 |
| F | 5.4 | 6.2 | 0.212 | 0.244 |
| G | 1.65 | 2.13 | 0.065 | 0.084 |
| H | - | 4.5 | - | 0.177 |
| J | 1.0 | 1.4 | 0.040 | 0.055 |
| K | 10.8 | 11.0 | 0.426 | 0.433 |
| L | 4.7 | 5.3 | 0.185 | 0.209 |
| M | 0.4 | 0.8 | 0.016 | 0.031 |
| N | 1.5 | 2.49 | 0.087 | 0.102 |

| Symbol | Characteristics | Maximum Ratings | Unit |
|------------|--|------------------------------|---------------------------|
| $I_{(AV)}$ | Maximum Average Forward Rectified Current @ $T_c=125^\circ\text{C}$ | 30 | A |
| I_{FSM} | Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD) | 250 | A |
| dv/dt | Voltage Rate Of Change (Rated V_R) | 10000 | V/us |
| V_F | Maximum Forward Voltage (Note 1) $I_F=15\text{A} @ T_J=25^\circ\text{C}$ $I_F=15\text{A} @ T_J=125^\circ\text{C}$ $I_F=30\text{A} @ T_J=25^\circ\text{C}$ $I_F=30\text{A} @ T_J=125^\circ\text{C}$ | 0.85 0.70 0.98 0.85 | V |
| I_R | Maximum DC Reverse Current @ $T_J=25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_J=125^\circ\text{C}$ | 0.05 10 | mA |
| R_{eJC} | Typical Thermal Resistance (Note 2) | 2.2 | $^\circ\text{C}/\text{W}$ |
| C_J | Typical Junction Capacitance Per Element (Note 3) | 700 | pF |
| T_J | Operating Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |

NOTES: 1. 300us Pulse Width, Duty Cycle 2%.

2. Thermal Resistance Junction To Case.

3. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

FEATURES

- * Metal of silicon rectifier, majority carrier conductor
- * Guard ring for transient protection
- * Low power loss, high efficiency
- * High current capability, low V_F
- * High surge capacity
- * For use in low voltage, high frequency inverters, free whelling, and polarity protection applications

MECHANICAL DATA

- * Case: TO-247AD molded plastic
- * Polarity: As marked on the body
- * Weight: 0.2 ounces, 5.6 grams
- * Mounting position: Any

Silicon **r**ectifier®

MBR30100PT thru MBR30200PT

Wide Temperature Range and High $T_{j\text{m}}$ Schottky Barrier Rectifiers

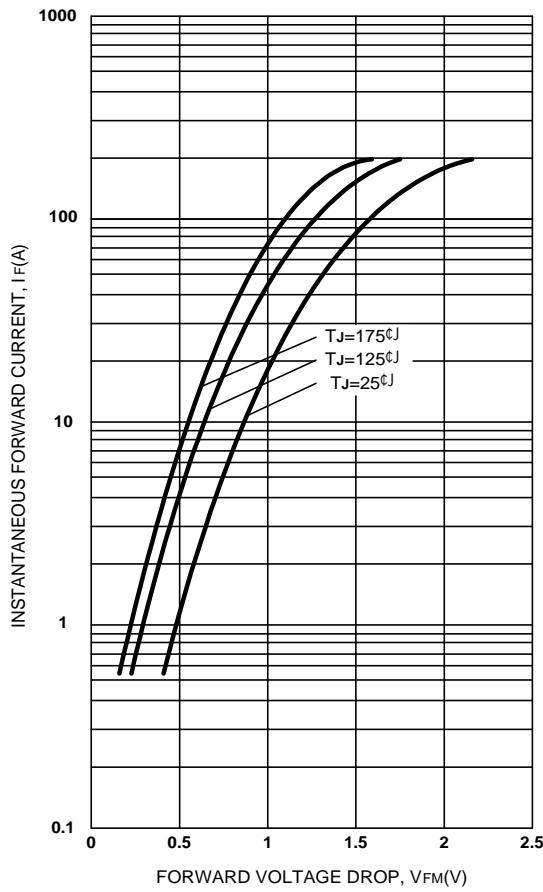


Figure 1. Max. Forward Voltage Drop Characteristics (Per Leg)

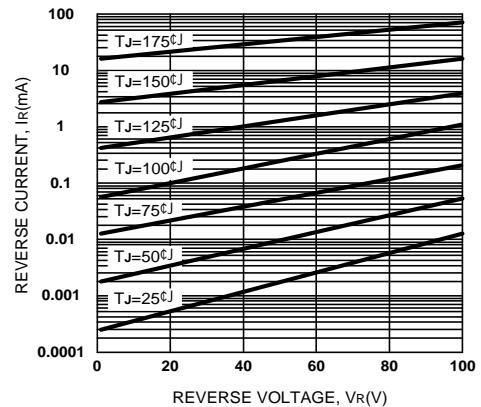


Figure 2. Typical Values Of Reverse Current Vs. Reverse Voltage (Per Leg)

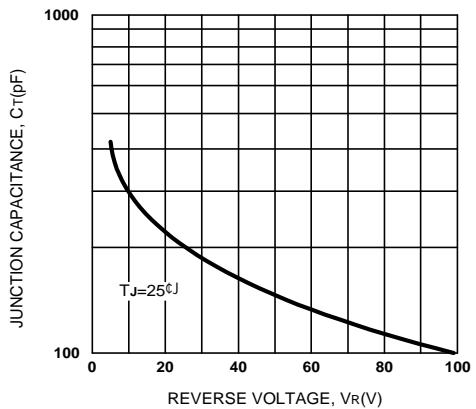


Figure 3. Typical Junction Capacitance Vs. Reverse Voltage (Per Leg)

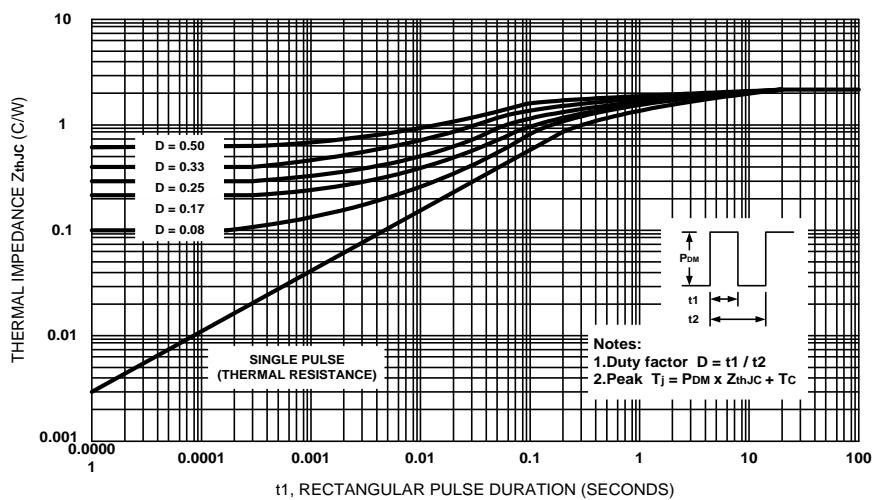


Figure 4. Max. Thermal Impedance Z_{thJC} Characteristics (Per Leg)

MBR30100PT thru MBR30200PT

Wide Temperature Range and High $T_{j\text{m}}$ Schottky Barrier Rectifiers

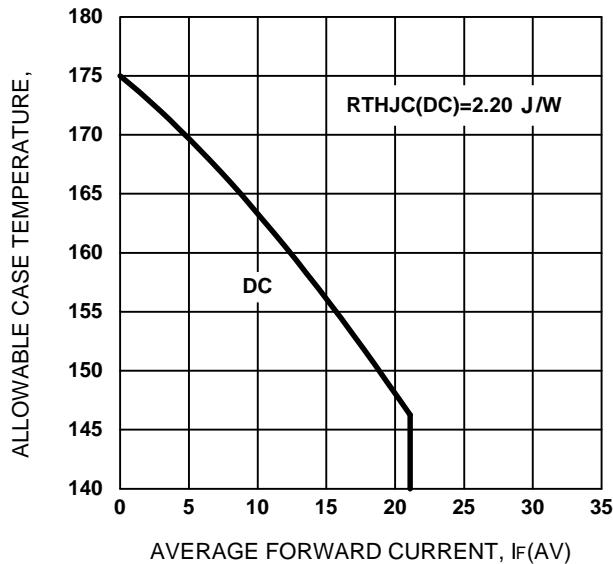


Figure 5. Max. Allowable Case Temperature Vs. Average Forward Current (Per Leg)

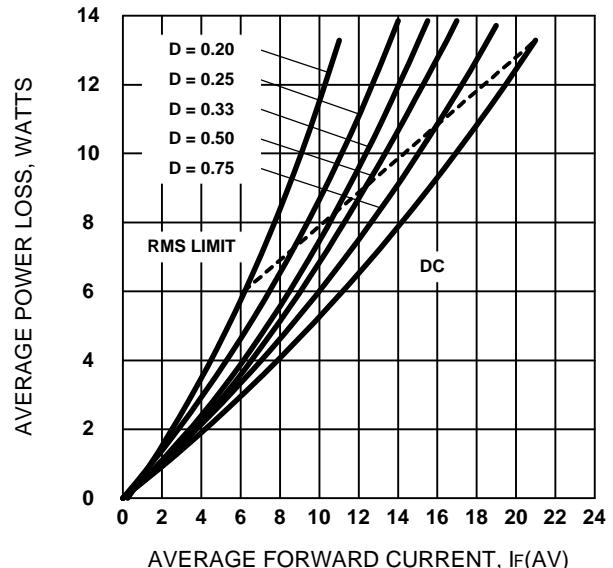


Figure 6. Forward PowerLoss Characteristics (Per Leg)

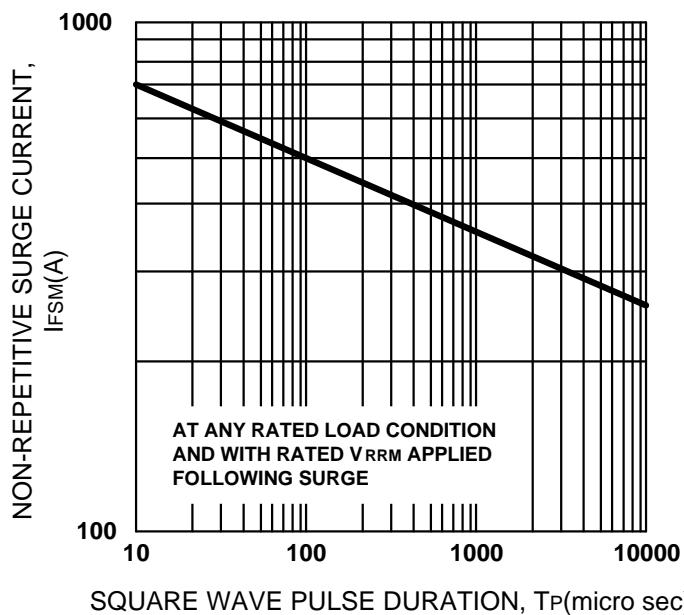


Figure 7. Max. Non-Repetitive Surge Current (Per Leg)